

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

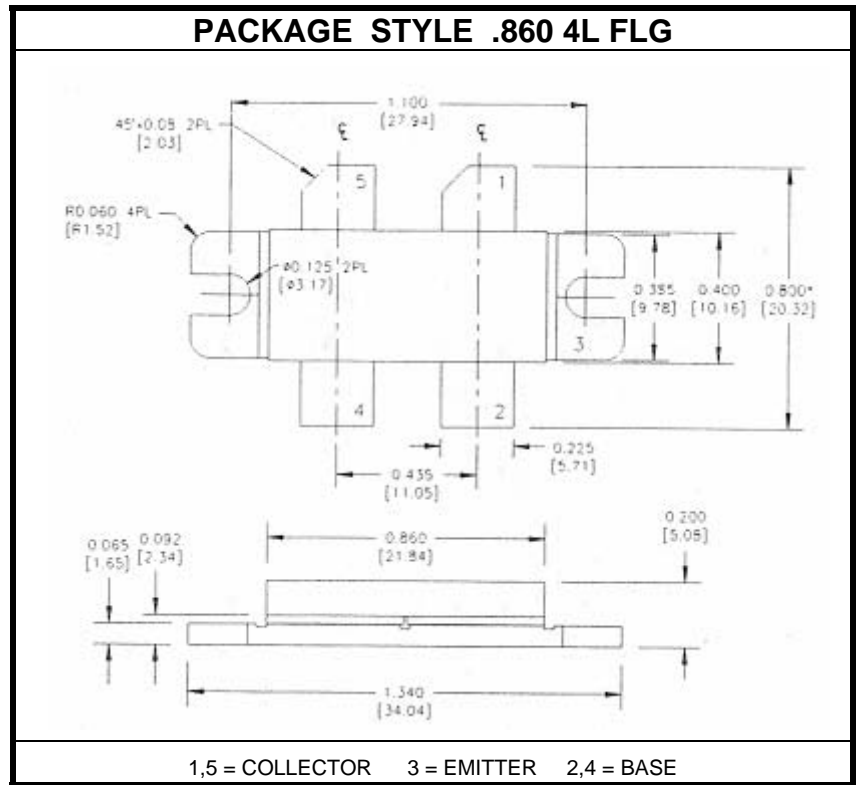
The **ASI PTB20101** is Designed for General Purpose Class AB Power Amplifier Applications up to 860 MHz.

FEATURES:

- 175 W, 470-860 MHz
- Silicon Nitride Passivated
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	20 A
V_{CB0}	65 V
P_{DISS}	330 W @ T _C = 25 °C
T_J	-40 °C to +150 °C
T_{STG}	-40 °C to +150 °C
θ_{JC}	0.53 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 100 mA			25			V
BV_{CES}	I _C = 100 mA			55			V
BV_{EBO}	I _E = 5.0 mA			3.5			V
h_{FE}	V _{CE} = 5.0 V	I _C = 1.0 A		20		100	---
C_{OB}	V _{CB} = 28 V		f = 1.0 MHz	3.5	5		pF
P_G	V _{CC} = 28 V	P _{OUT} = 110 W	f = 860 MHz	8.5	11		dB
η_C	I _{CQ} = 2x200 mA			55	58		%
P_{OUT}				175			W
Ψ	V _{CC} = 28 V	P _{OUT} = 175 W	f = 860 MHz			5:1	---
	I _{CQ} = 2x200 mA						